

### Features

- Low capacitance: 0.35pF typical (I/O to GND)
- Very high peak pulse power at Vbus (2500W)
- Up to 3 data lines and one power line protects
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test  
Air discharge: ±30kV (Vbus) / 16kV (data lines)  
Contact discharge: ±30kV (Vbus) / 10kV (data lines)
  - IEC61000-4-4 (EFT) 40A (5/50ns)
  - IEC61000-4-4 (Lightning) 100A (Vbus, 8/20µs) / 4A (data lines, 8/20µs)
- RoHS Compliant

### Description

The ESD0541LT is a low capacitance TVS array,utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines.The ESD0541LT complies with the IEC 61000-4-2 (ESD) standard with ±15kV air and ±8kV contact discharge. It is assembled into a 6-pin DFN2018-6 lead-free package. The leads are finished with NiPdAu. Each device will protect up to four high-speed lines. The combination of small size, low capacitance, and high surge capability makes them ideal for use in applications such as USB ports.

### Mechanical Characteristics

- Package: DFN2018-6
- Lead Finish: NiPdAu
- Case Material: “Green” Molding Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram

### Applications

- USB 2.0
- USB OTG
- µUSB

### Part Number Code

<b>E</b>	<b>S</b>	<b>D</b>	<b>0</b>	<b>5</b>	<b>1</b>	<b>1</b>	<b>L</b>	<b>1</b>
<b>1</b>	<b>2</b>	<b>3</b>	<b>4</b>	<b>5</b>	<b>6</b>	<b>7</b>	<b>8</b>	<b>9</b>

Product Type	
ESD	TSK Electrostatic suppressor ESD Type

Reverse Working Voltage (V)	
3V3	3.3V
05	5V
16	16V

Line	
1	1-Line
2	2-Line
3	3-Line

Capacitance Type	
L	Low
X	Normal

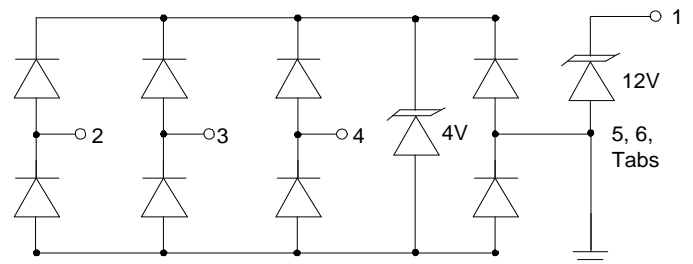
directional	
0	Bi
1	Uni

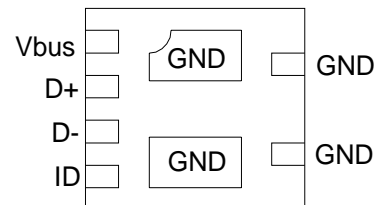
Size	
1	0201
2	0402
3	DFN0603
4	DFN1006

★ Code 4 to 9 is optional

### Dimensions and Pin Configuration



Circuit Diagram



Pin Schematic

### Absolute Maximum Ratings ( $T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
<b>DP, DM, USB ID (Pins 2, 3, 4)</b>			
Peak Pulse Power (8/20 $\mu\text{s}$ )	Ppk	60	W
Peak Pulse Current (8/20 $\mu\text{s}$ )	I <sub>PP</sub>	4	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V <sub>ESD</sub>	$\pm 16$ $\pm 10$	kV
Operating Temperature Range	T <sub>J</sub>	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	$^{\circ}\text{C}$
<b>Vbus (Pin 1)</b>			
Peak Pulse Power (8/20 $\mu\text{s}$ )	Ppk	2500	W
Peak Pulse Current (8/20 $\mu\text{s}$ )	I <sub>PP</sub>	100	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V <sub>ESD</sub>	$\pm 30$ $\pm 30$	kV
Operating Temperature Range	T <sub>J</sub>	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	$^{\circ}\text{C}$

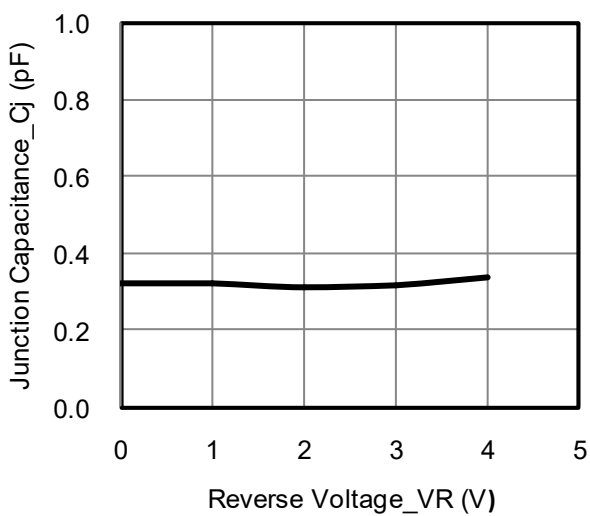
### Electrical Characteristics ( $T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
<b>DP, DM, USB ID (Pins 2, 3, 4)</b>						
Reverse Working Voltage	V <sub>RWM</sub>			4	V	Any I/O to ground
Breakdown Voltage	V <sub>BR</sub>	4.5			V	I <sub>T</sub> = 1mA, any I/O to ground
Reverse Leakage Current	I <sub>R</sub>			0.1	$\mu\text{A}$	V <sub>RWM</sub> = 4V, any I/O to ground
Clamping Voltage	V <sub>C</sub>			10.5	V	I <sub>PP</sub> = 1A (8 x 20 $\mu\text{s}$ pulse), any I/O pin to ground
Clamping Voltage	V <sub>C</sub>			15.0	V	I <sub>PP</sub> = 4A (8 x 20 $\mu\text{s}$ pulse), any I/O pin to ground
Junction Capacitance	C <sub>J</sub>		0.35	0.5	pF	V <sub>R</sub> = 0V, f = 1MHz, any I/O pin to ground

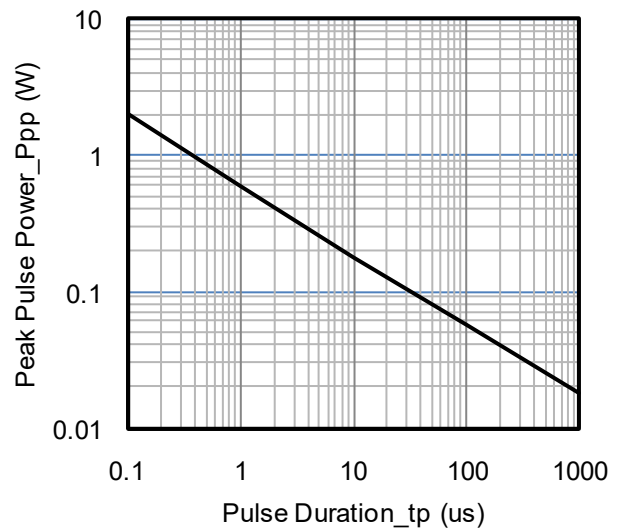
Note: I/O Pins are 2, 3, 4

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
<b>Vbus TVS (Pin 1)</b>						
Reverse Working Voltage	VRWM			12	V	Pin 1 to ground
Breakdown Voltage	VBR	12.5	13.3	16.5	V	IT = 1mA, pin 1 to ground
Reverse Leakage Current	IR			0.2	μA	VRWM = 12V, pin 1 to ground
Forward Voltage	VF	0.6	0.7	1.0	V	IF = 10mA, ground to pin 1
Clamping Voltage	VC			18	V	I <sub>PP</sub> = 30A (8 x 20μs pulse), pin 6 to ground
Clamping Voltage	VC			25	V	I <sub>PP</sub> = 100A (8 x 20μs pulse), pin 6 to ground
Junction Capacitance	CJ			1000	pF	VR = 0V, f = 1MHz, pin 6 to ground

**Typical Performance Characteristics (TA=25°C unless otherwise Specified)**

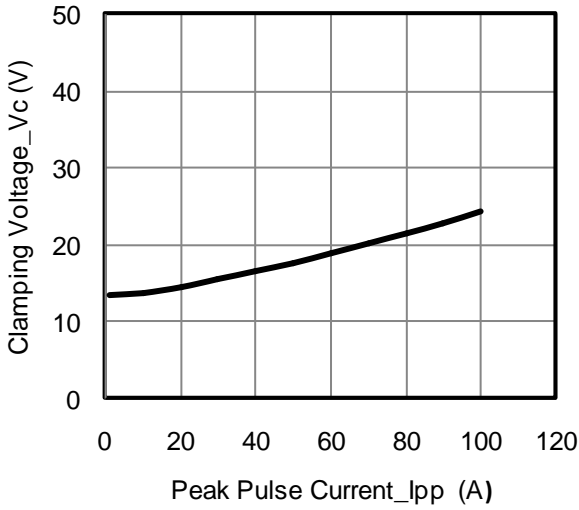


**Junction Capacitance vs. Reverse Voltage (Pins 2, 3, 4)**

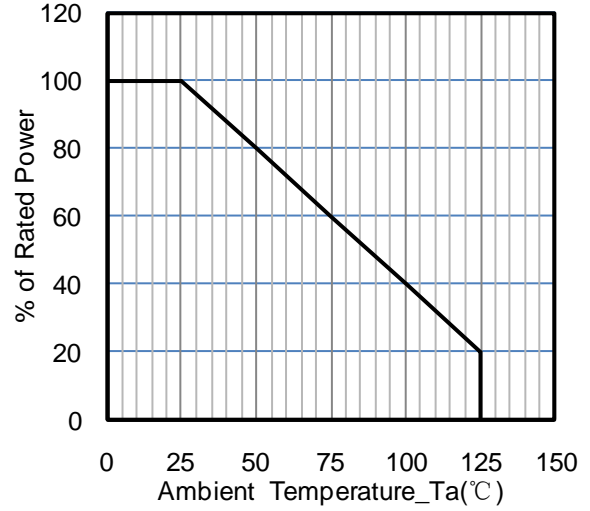


**Peak Pulse Power vs. Pulse Time**

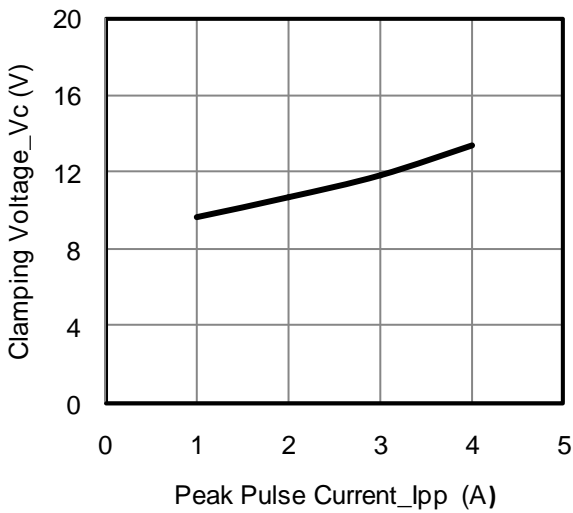
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



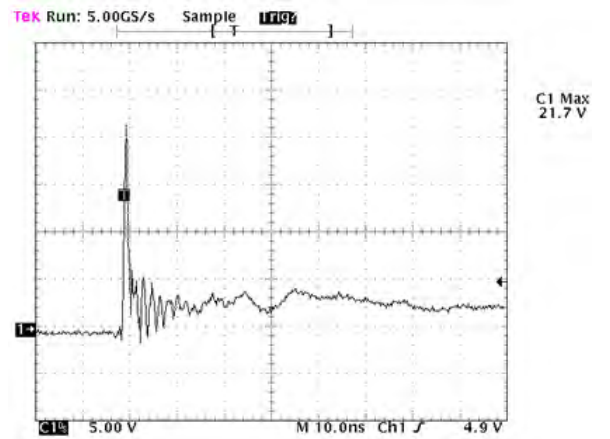
Clamping Voltage vs. Peak Pulse Current (Vbus)



Power Derating Curve

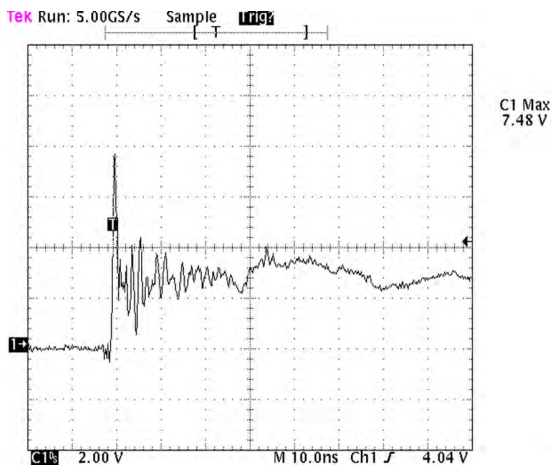


Clamping Voltage vs. Peak Pulse Current (Pins 2, 3, 4)



ESD Clamping Voltage

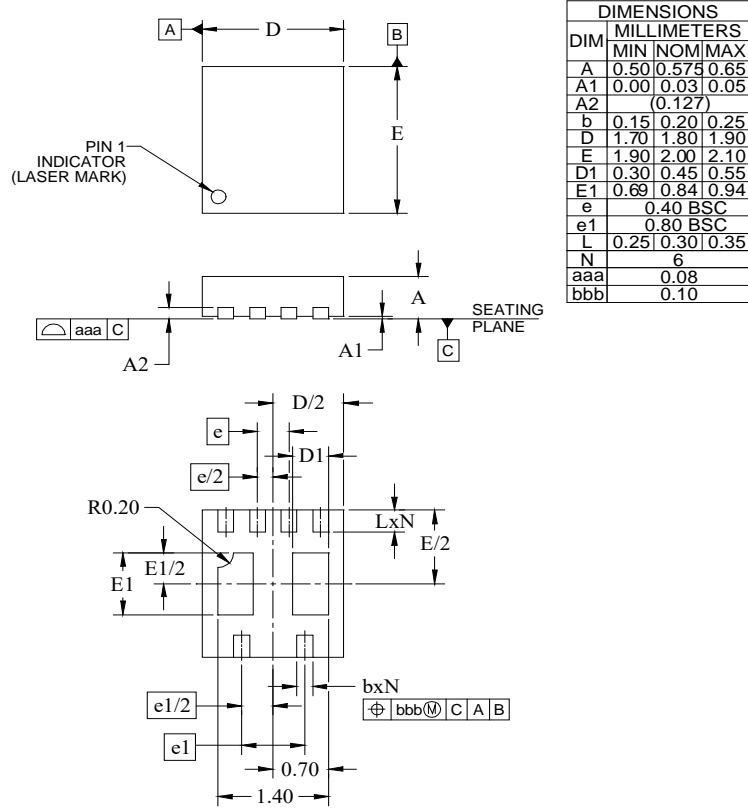
8 kV Contact per IEC61000-4-2 (Pins 2, 3, 4)



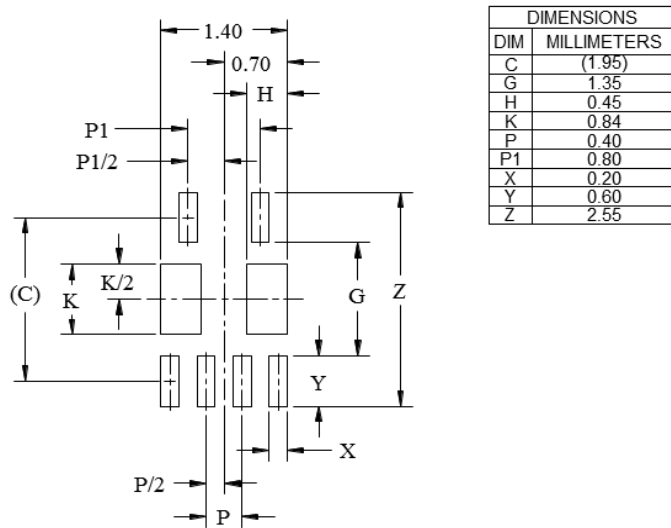
ESD Clamping Voltage

8 kV Contact per IEC61000-4-2 (Vbus)

DFN2018 6 Package Outline Drawing



Suggested Land Pattern



Ordering Information

Part Number	Packaging	Reel Size
ESD0541LT	3000/Tape & Reel	7 inch